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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Wu et al.

Attorney Docket No.:
NOVLP098/NVLS-002907

Application No.: 10/800,409

Examiner: Chen, B.

Filed: March 11, 2004

Group: 1762

Title: METHODS FOR PRODUCING LOW-K
CDO FILMS

Confirmation No.: 7038

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as first-class mail on March 24, 2006 in an envelope addressed to the Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450

Signed: _____

Tara Hayden

**INFORMATION DISCLOSURE STATEMENT
BEFORE FINAL ACTION OR NOTICE OF ALLOWANCE
(37 CFR §§ 1.56 AND 1.97(c))**

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

The references listed in the attached PTO Form 1449, a copy of which is attached, may be material to examination of the above-identified patent application. Applicants submit this reference in compliance with their duty of disclosure pursuant to 37 CFR §§ 1.56 and 1.97. The Examiner is requested to make this citation of official record in this application.

Several items were lined out and not initialed as considered in the Information Disclosure Statement (IDS) filed on July 14, 2004, July 23, 2005, August 22, 2005 and October 17, 2005. Also being submitted with this IDS are clean copies of the PTO 1449 forms previously submitted that were not initialed by the Examiner. Per a conversation with James E. Austin on January 20, 2006, the Examiner agreed to indicate the references listed in clean copies if these PTO 1449 forms were submitted. The Examiner is respectfully requested to indicate his consideration of these documents in the next action by initialing next to it on the PTO Form-1449.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that this reference indeed constitutes prior art.

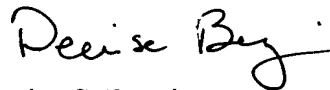
This Information Disclosure Statement is being filed after the mailing date of the first Office Action on the merits, or after three months of the filing date of this application, whichever event occurred last, but it is believed before the mailing date of either: (i) a final action under §1.113 or (ii) a notice of allowance under §1.311, whichever occurs first.

Accompanying this Information Disclosure Statement is

- ☐ a statement as specified in 37 CFR 1.97(e); or
☒ the fee set forth in 37 CFR 1.17(p).

If fees are due, enclosed is our Check No. 11760 for \$180.00 in payment of the Information Disclosure Statement Fee. If it is determined that any additional fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 500388 (Order No. NOVLP098).

Respectfully submitted,
BEYER WEAVER & THOMAS, LLP



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| Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary) | Atty Docket No. NOVLP098 | Application No.: 10/800,409 |
| | Applicant: Wu et al. Filing Date 03-11-2004 | Group 1762 |

U.S. Patent Documents

| Examiner Initial | No. | Patent No. | Date | Patentee | Class | Sub-class | Filing Date |
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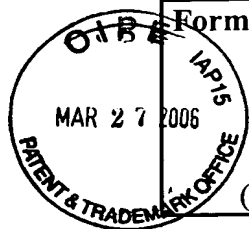
Foreign Patent or Published Foreign Patent Application

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub-class | Translation | |
|------------------|-----|--------------|------------------|--------------------------|-------|-----------|-------------|----|
| | | | | | | | Yes | No |
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| | C1 | U.S. Office Action mailed December 27, 2005, from U.S. Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-002919]. |
| | C2 | U.S. Office Action mailed February 7, 2006, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821]. |
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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| Examiner | | Date Considered |

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| Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary) | Atty Docket No. NOVLP098 | Application No.: 10/800,409 |
| | Applicant: Wu et al. Filing Date 03-11-2004 | Group 1762 |

U.S. Patent Documents

| Examiner Initial | No. | Patent No. | Date | Patentee | Class | Sub-class | Filing Date |
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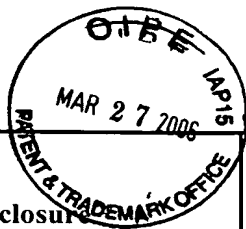
Foreign Patent or Published Foreign Patent Application

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub-class | Translation | |
|------------------|-----|--------------|------------------|--------------------------|-------|-----------|-------------|----|
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| | C1 | U.S. Office Action mailed July 13, 2005, from U.S Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-000820]. |
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| Examiner | | Date Considered |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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